# 10V Drive Nch MOSFET

## **RDD050N20**

### Structure

Silicon N-channel **MOSFET** 

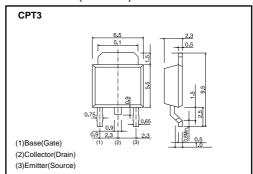
### ● Features

- 1) Low on-resistance.
- 2) Low input capacitance.
- 3) Exellent resistance to damage from static electricity.

### Application

Switching

### ●Dimensions (Unit:mm)



### Packaging specifications

	Package	Taping
Туре	Code	TL
	Basic ordering unit (pieces)	2500
RDD050N2	0	

### ● Absolute maximum ratings (Ta=25°C)

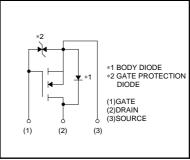
Parameter		Symbol	Limits	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	200	V	
Gate-Source Voltage		Vgss	±30	V	
Dunin Comment	Continuous	I <sub>D</sub>	±5	Α	
Drain Current	Pulsed	I <sub>DP</sub> *1	±20	Α	
Source Current (Body Diode)	Continuous	Is	5	Α	
	Pulsed	I <sub>SP</sub> *1	20	А	
Avalanche Current		I <sub>AS</sub> *2	5	Α	
Avalanche Energy		E <sub>AS</sub> *2	75	mJ	
Total Power Dissipation (Tc=25°C)		Po	20	W	
Channel Temperature		Tch	150	°C	
Storage Temperature		T <sub>stg</sub>	-55 to +150	°C	

<sup>\*1</sup> Pw ≤ 10μs, Duty cycle ≤ 1% \*2 L≒ 4.5mH, Vbb=50V, Rg=25Ω, 1Pulse, Tch=25°C

### Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	6.25	°C/W

### ●Equivalent Circuit



\*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-Source Leakage	Igss	_	_	±10	μΑ	Vgs=±30V, Vps=0V
Drain-Source Breakdown Voltage	V(BR) DSS	200	_	_	V	I <sub>D</sub> =1mA, V <sub>G</sub> s=0V
Zero Gate Voltage Drain Current	IDSS	_	_	25	μΑ	VDS=200V, VGS=0V
Gate Threshold Voltage	VGS (th)	2.0	_	4.0	V	VDS=10V, ID=1mA
Static Drain-Source On-State Resistance	RDS (on)	_	0.55	0.72	Ω	Ib=2.5A, Vgs=10V
Forward Transfer Admittance	Yfs *	1.1	1.8	_	S	Vps=10V, Ip=2.5A
Input Capacitance	Ciss	_	292	_	pF	Vps=10V
Output Capacitance	Coss	_	92	_	pF	V <sub>G</sub> s=0V
Reverse Transfer Capacitance	Crss	_	28	_	pF	f=1MHz
Turn-On Delay Time	td (on) *	_	10	_	ns	I <sub>D</sub> =2.5A, V <sub>D</sub> D ≑100V
Rise Time	tr *	_	22	_	ns	Vgs=10V
Turn-Off Delay Time	td (off) *	_	23	_	ns	RL=40Ω
Fall Time	t <sub>f</sub> *	_	28	_	ns	R <sub>G</sub> =10Ω
Total Gate Charge	Qg *	_	9.3	_	nC	V <sub>DD</sub> =100V
Gate-Source Charge	Qgs *	_	2.8	_	nC	Vgs=10V
Gate-Drain Charge	Q <sub>gd</sub> *	_	3.7	_	nC	In=5A

<sup>\*</sup> Pulsed

### ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp *	_	_	1.5	V	I <sub>S</sub> = 5.0A, V <sub>GS</sub> =0V
Reverse recovery time	trr	_	117	_	ns	IDR= 5.0A, VGS=0V
Reverse recovery charge	Qrr	-	0.37	_	μС	di/dt= 100A / μs

<sup>\*</sup> Pulsed

### •Electrical characteristic curves

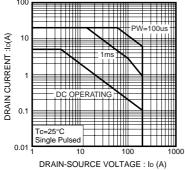


Fig.1 Maximum Safe Operating Area

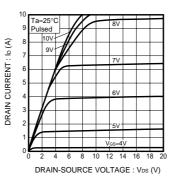


Fig.2 Typical Output Characteristics

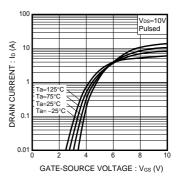


Fig.3 Typical Transfer Characteristics

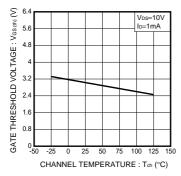


Fig.4 Gate Threshold Voltage vs. Channel Temperature

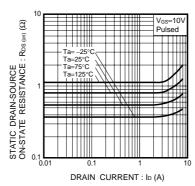


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

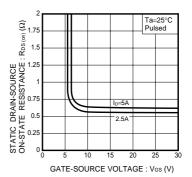


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

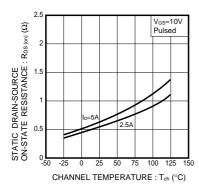


Fig.7 Static Drain-Source On-State Resistance vs. Channel Temperature

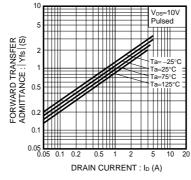


Fig.8 Forward Transfer Admittance vs. Drain Current

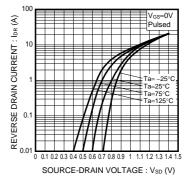


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

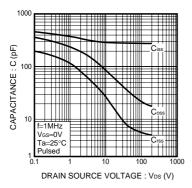


Fig.10 Typical Capacitance vs. Drain-Source Voltage

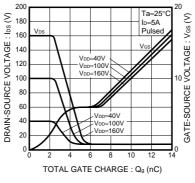


Fig.11 Dynamic Input Characteristics

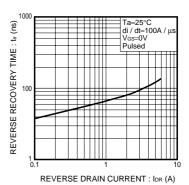


Fig.12 Reverse Recovery Time vs. Reverse Drain Current

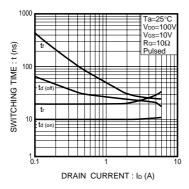


Fig.13 Switching Characteristcs

### •Switching characteristics measurement circuit

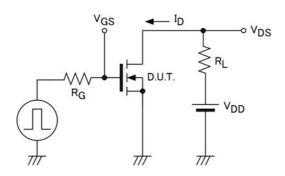


Fig.1-1 Switching time measurement circuit

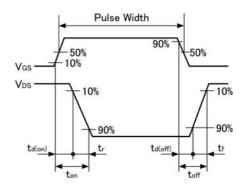


Fig.1-2 Switching waveforms

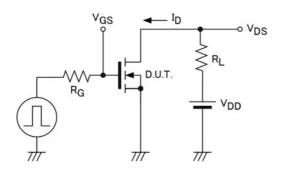


Fig.2-1 Gate charge measurement circuit

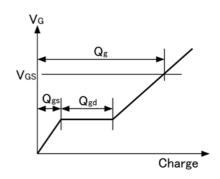


Fig.2-2 Gate charge waveform

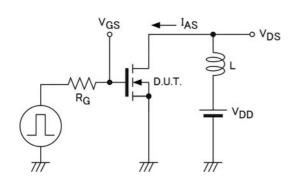


Fig.3-1 Avalanche measurement circuit

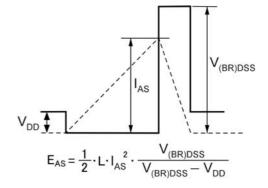


Fig.3-2 Avalanche waveform

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